# **Electrical Parameters**

Compared to surge suppression using other technologies, P Series devices offer absolute surge protection

regardless of the surge current available and the rate of applied voltage (dv/dt). P Series devices:

- · Cannot be damaged by voltage
- Eliminate hysteresis and heat dissipation typically found with clamping devices
- · Eliminate voltage overshoot caused by fast-rising transients
- Are non-degenerative
- Will not fatigu
- · Have low capacitance, making them ideal for high-speed transmission equipment

#### **Floctrical Parameters**

Parameter	Definition		+I	
<b>C</b> 0	<b>Off-state Capacitance</b> — typical capacitance		<b>A</b> .	
	measured in off state			
di/dt	Rate of Rise of Current — maximum rated value of		Ιτ	
	the acceptable rate of rise in current over time			
Is	Switching Current — maximum current required to			
	switch to on state		Is	<i>j</i>
<b>I</b> DRM	Leakage Current — maximum peak off-state current		Ін	
	measured at VDRM			/
$\mathbf{I}_{\mathrm{H}}$	Holding Current — minimum current required to			
	maintain on state		I DRM	
$\mathbf{I}_{\mathrm{PP}}$	Peak Pulse Current — maximum rated peak impulse -V	t		
	Current		VT	VDRM VS
IT	<b>On-state Current</b> — maximum rated continuous	/		
	on-state current	/		
<b>I</b> TSM	Peak One-cycle Surge Current — maximum rated	1		
	one-cycle AC current	1		
Vs	Switching Voltage — maximum voltage prior to	1		
	switching to on state			
<b>V</b> DRM	Peak Off-state Voltage — maximum voltage that can			
	be applied while maintaining off state			
VF	On-state Forward Voltage — maximum forward			
	voltage measured at rated on-state current			
VT	<b>On-state Voltage</b> — maximum voltage measured at		' ↓	
	Rated on-state current		-I	

machines, and other CPE.

P Series solid state protection devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K. 20, K. 21 and K. 45, IEC 60950, UL 60950, and TIA-968 (formerly known as FCC Part 68).

P Series solid state protection thyristor protect telecommunications equipment such as modems, line cards, fax

#### **Over-voltage Protection Thyristor**

#### **Over-voltage Protection Thyristor**

Description

ROHS

1

**SP2300EC** 



P Series

Over-voltage Protection Thyristor				r	SP2300EC					ROHS
F	Electrical Cha	racterist	ics							
	Part	Vdrm	Vs	VT	Idrm	Is	Ιτ	Ін	Co	
_	Number	Volts	Volts	Volts	μAmps	mAmps	Amps	mAmps	pF	
	SP2300EC	190	260	4	5	800	2. 2	150	65	

\* For surge ratings, see table below.

Notes:

• All measurements are made at an ambient temperature of 25°C. IPP applies to -40°C through +85°C temperature range.

• Off-state capacitance (Co) is measured at 1 MHz with a 2 V bias and is typical value.

#### Surge Ratings

Series	I₽₽ 2/10 µs Amps	Ipp 8/20 µs Amps	Ipp 10/160 µs Amps	Ipp 10∕560 µs Amps	Ipp 10/1000 µs Amps	Ітям 60 Hz Amps	di/dt Amps/µs
С	500	400	200	150	100	50	500

### Thermal Considerations

Package T0-92	Symbol	Parameter	Value	Unit
	TJ	Operating Junction Temperature	-40 to +150	Ĉ
2	Ts	Storage Temperature Range	-40 to +150	C
	R e ja	Junction to Ambient on printed circuit	90	°C/W



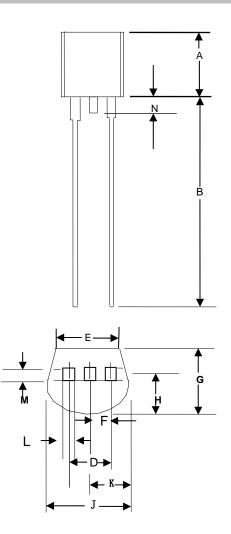
# Over-voltage Protection Thyristor

**P** Series

ROHS

# SP2300EC

Dimensions



Dimonsion	In	ches	Millimeters		
Dimension	MIN	MIN	MIN	MIN	
А	0.176	0. 196	4. 47	4. 98	
В	0.5		12. 7		
D	0. 095	0. 105	2.14	2.67	
E	0.15		3. 81		
F	0.046	0.054	1.16	1. 37	
G	0. 135	0. 145	3. 43	3. 68	
Н	0.088	0.096	2. 23	2.44	
J	0.176	0. 186	4. 47	4. 73	
K	0.088	0.096	2. 23	2.44	
L	0. 013	0.019	0. 33	0.48	
М	0. 013	0.017	0. 33	0. 43	
N		0.06		1. 52	



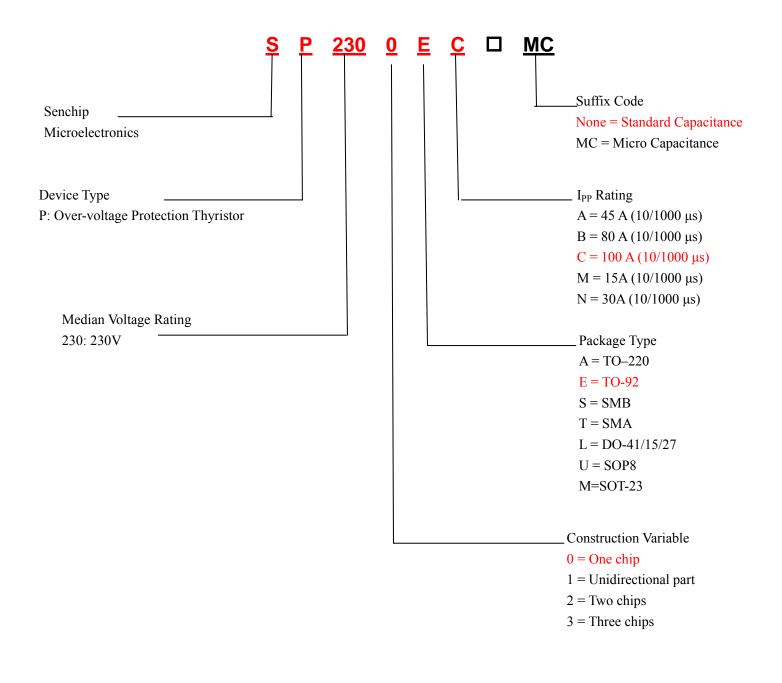


ROHS

#### **Over-voltage Protection Thyristor**

## SP2300EC

#### Description of Part Number



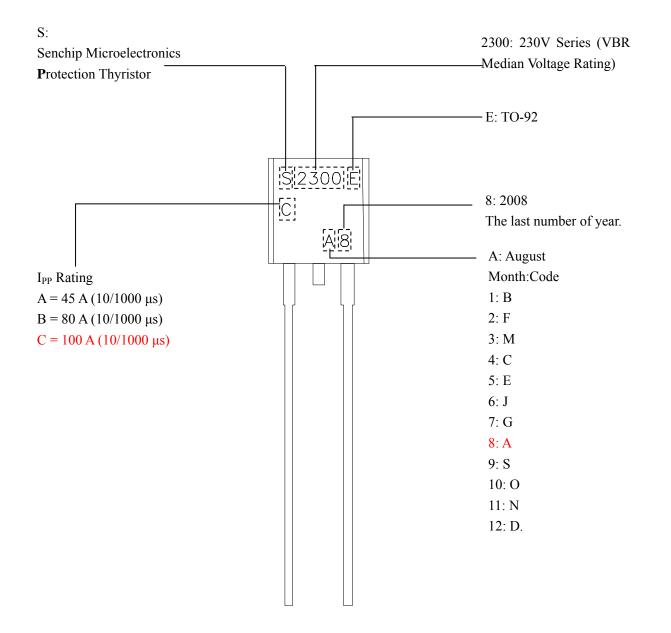


ROHS

### **Over-voltage Protection Thyristor**

# SP2300EC

### Description of Marking





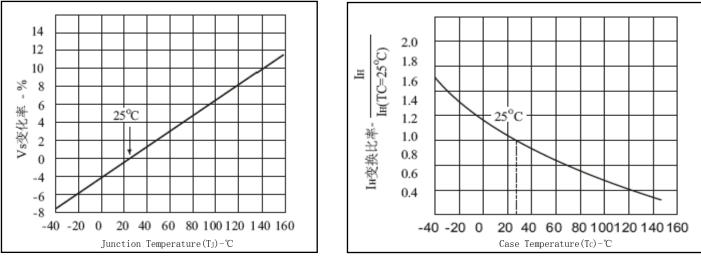
## **P** Series

ROHS

<b>Over-voltage Protectio</b>	SP2300EC						
Summary of Packing Options							
Package Type	Description	Packing					

Package Type	Description	Packing	Industry
		Quantity	Standard
T0-92	Bulk Pack	2000 PCS	N/A
EA, EB, EC			

### Thermal Derating Curves



Normalized VS Change versus Junction Temperature

Normalized DC Holding Current versus Case Temperature

